





50V DUAL NPN SILICON LOW SATURATION SWITCHING TRANSISTOR

Features

- BV_{CEO} > 50V
- $R_{\text{SAT}} = 160 \text{mV}$
- Max continuous Current $I_C = 1A$
- Low Equivalent On Resistance
- Low Saturation Voltage
- Lead Free, RoHS Compliant (Note 1)
- Halogen and Antimony Free "Green" Device (Note 2)
- Qualified to AEC-Q101 Standards for High Reliability

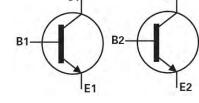
Applications

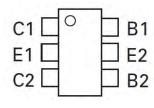
- LCD Backlighting inverter circuits
- Boost functions in DC-DC converters

Mechanical Data

- Case: SOT26
- Case material: Molded Plastic. "Green" Molding Compound.
- UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Matte Tin Finish
- Weight: 0.018 grams (Approximate)







SOT26

Device symbol

Pin out -top view

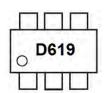
Ordering Information (Note 3 & 4)

Product	Grade	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
ZXTD09N50DE6TA	Commercial	D619	7	8	3,000
ZTD09N50DE6QTA	Automotive	D619	7	8	3,000

Notes:

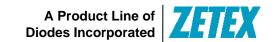
- No purposefully added lead.
 Diodes Inc.'s "Green" Policy can be found on our website at http://www.diodes.com
- 3. For more packaging details, go to our website at http://www.diodes.com.
- 4. Products with Q-suffix are automotive grade.

Marking Information



D619 = Product type Marking Code





Absolute Maximum Ratings @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	50	V
Collector-Emitter Voltage	V_{CEO}	50	V
Emitter-Base Voltage	V_{EBO}	5	V
Continuous Collector Current	Ic	1	Α
Base current	I _B	200	mA
Peak Pulse Current	I _{CM}	2	Α

Thermal Characteristics @TA = 25°C unless otherwise specified

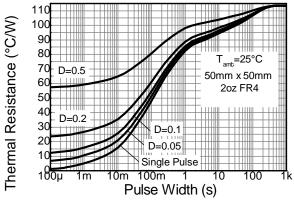
Characteristic	Symbol	Value	Unit		
Danier Dissipation	(Note 5 & 8)		0.90 7.2		
Power Dissipation Linear derating factor	(Note 5 & 9)	P _D	1.1 8.8	W mW /°C	
	(Note 6 & 8)		1.7 13.6		
	(Note 5 & 8)		139	°C/W	
Thermal Resistance, Junction to Ambient	(Note 5 & 9)	$R_{ heta JA}$	73		
	(Note 6 & 8)		113		
Thermal Resistance, Junction to Lead	(Note 10)	R ₀ JL	75.52	°C/W	
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C		

Notes:

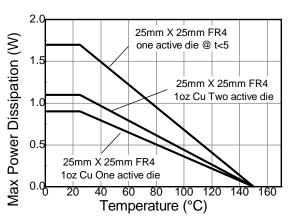
- 5. For a device surface mounted on 25mm X 25mm FR4 PCB with high coverage of single sided 1 oz copper, in still air conditions
- 6. For a device surface mounted on FR4 PCB measured at < 5sec
- 7. Repetitive rating pulse width limited by maximum junction temperature. Refer to transient thermal impedance graph
- 8. For a device with one active die
- 9. For a device with two die running at equal power
- 10. Thermal resistance from junction to solder-point (at the end of the collector lead).



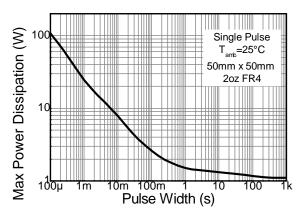
Thermal Characteristics



Transient Thermal Impedance

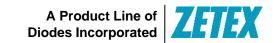


Derating Curve



Pulse Power Dissipation





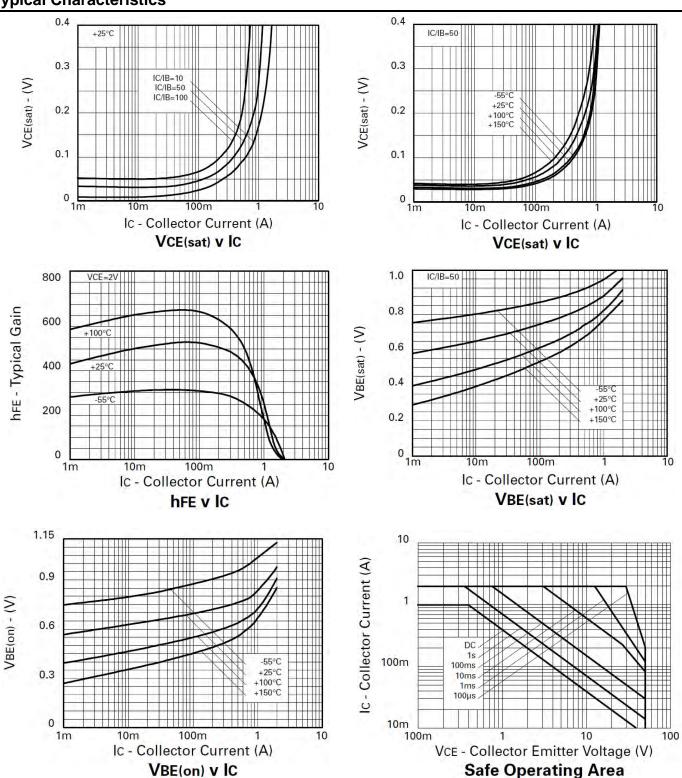
Electrical Characteristics @TA = 25°C unless otherwise specified (Q1, Q2 common)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV _{CBO}	50			V	$I_{C} = 100 \mu A$
Collector-Emitter Breakdown Voltage (Note 11)	BV _{CEO}	50			V	$I_C = 10mA$
Emitter-Base Breakdown Voltage	BV _{EBO}	5			V	$I_E = 100 \mu A$
Collector-Base Cutoff Current	I _{CBO}			10	nA	$V_{CB} = 40V$
Collector-Emitter Cutoff Current	I _{CES}			10	nA	$V_{CES} = 40V$
Emitter Cutoff Current	I _{EBO}			10	nA	$V_{EB} = 4V$
DC Current Gain (Note 11)	h _{FE}	200 300 200 75 20	420 450 350 130 60			$\begin{split} I_C &= 10 \text{mA}, \ V_{CE} = 2 \text{V} \\ I_C &= 100 \text{mA}, \ V_{CE} = 2 \text{V} \\ I_C &= 500 \text{mA}, \ V_{CE} = 2 \text{V} \\ I_C &= 14, \ V_{CE} = 2 \text{V} \\ I_C &= 1.5 \text{A}, \ V_{CE} = 2 \text{V} \end{split}$
Collector-Emitter Saturation Voltage (Note 11)	$V_{CE(sat)}$		24 60 120 160	35 80 200 270	mV	$I_C = 100$ mA, $I_B = 10$ mA $I_C = 250$ mA, $I_B = 10$ mA $I_C = 500$ mA, $I_B = 10$ mA $I_C = 1$ A, $I_B = 50$ mA
Base-Emitter Saturation Voltage (Note 11)	$V_{BE(sat)}$		940	1100	mV	$I_C = 1A, I_B = 50mA$
Base-Emitter Turn-On Voltage (Note 11)	$V_{BE(on)}$		850	1100	mV	$I_C = 1A$, $V_{CE} = 2V$
Output Capacitance	C_{obo}		10		pF	$V_{CB} = 10V. f = 1MHz$
Current Gain-Bandwidth Product	f⊤		215		MHz	$V_{CE} = 10V, I_{C} = 50mA$ f = 100MHz
Turn-On Time	t _{on}		150		ns	$V_{CC} = 10V, I_{C} = 1A$
Turn-Off Time	t _{off}		425		ns	$I_{B1} = I_{B2} = 100 \text{mA}$

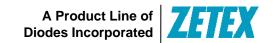
Notes: 11. Measured under pulsed conditions. Pulse width \leq 300 μ s. Duty cycle \leq 2%



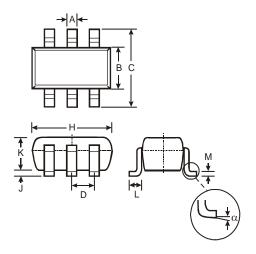
Typical Characteristics





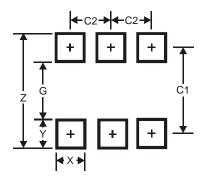


Package Outline Dimensions



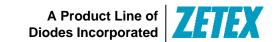
SOT26					
Dim	Min	Max	Тур		
Α	0.35	0.50	0.38		
В	1.50	1.70	1.60		
С	2.70	3.00	2.80		
D	_	_	0.95		
Н	2.90	3.10	3.00		
J	0.013	0.10	0.05		
K	1.00	1.30	1.10		
L	0.35	0.55	0.40		
М	0.10	0.20	0.15		
α	0°	8°			
All Dimensions in mm					

Suggested Pad Layout



Dimensions	Value (in mm)
Z	3.20
G	1.60
Х	0.55
Y	0.80
C1	2.40
C2	0.05





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